



AMD-G0186

Patent

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: ) Examiner: Le, D.  
Wang et al. )  
Serial No. 10/053,256 )  
Filed: January 18, 2002 )  
For: TWO-STEP SOURCE SIDE )  
IMPLANT FOR IMPROVING )  
SOURCE RESISTANCE AND )  
SHORT CHANNEL EFFECT )  
IN DEEP SUB- 0.18um FLASH )  
MEMORY TECHNOLOGY )

Commissioner of Patents  
Washington, D.C. 20231

AMENDMENT AND REMARKS IN RESPONSE TO OFFICE ACTION

Sir:

In response to the Office Action mailed August 14, 2002, please consider the following remarks and enter the following amendments.

IN THE CLAIMS

Please amend the Claims as follows:

1. (Amended) A method of manufacturing a flash memory Electrically-Erasable Programmable Read Only Memory (EEPROM) device having a lightly-doped source region near the critical gate region and a heavily-doped source region away from the